# Octal D Flip-Flop with Common Clock and Reset

# **High-Performance Silicon-Gate CMOS**

The MC74HC273A is identical in pinout to the LS273. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of eight D flip—flops with common Clock and Reset inputs. Each flip—flop is loaded with a low—to—high transition of the Clock input. Reset is asynchronous and active low.

#### **Features**

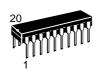
- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 264 FETs or 66 Equivalent Gates
- Pb-Free Packages are Available\*



# ON Semiconductor®

http://onsemi.com

# MARKING DIAGRAMS



PDIP-20 N SUFFIX CASE 738

20 AAAAAAAAAAA MC74HC273AN O AWLYYWWG

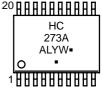


SOIC-20 DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E





SOEIAJ-20 F SUFFIX CASE 967

A = Assembly Location

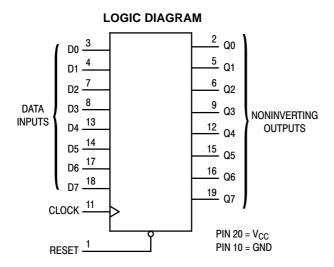
WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G = Pb−Free Package ■ = Pb−Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



RESET [	1●	20	] v <sub>cc</sub>
Q0 [	2	19	] Q7
D0 [	3	18	] D7
D1 [	4	17	] D6
Q1 [	5	16	] Q6
Q2 [	6	15	] Q5
D2 [	7	14	] D5
D3 [	8	13	] D4
Q3 [	9	12	] Q4
GND [	10	11	СГОСК

**PIN ASSIGNMENT** 

# **FUNCTION TABLE**

Inputs			Output
Reset	Clock	D	Q
L	Х	Х	L
Н		Н	Н
Н		L	L
Н	L	X	No Change
Н	~	Х	No Change

Design Criteria	Value	Units
Internal Gate Count*	66	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	.0075	рЈ

<sup>\*</sup>Equivalent to a two-input NAND gate.

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HC273AN	PDIP-20	18 Units / Rail
MC74HC273ANG	PDIP-20 (Pb-Free)	18 Units / Rail
MC74HC273ADW	SOIC-20 WIDE	38 Units / Rail
MC74HC273ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
MC74HC273ADWR2	SOIC-20 WIDE	1000 Tape & Reel
MC74HC273ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 Tape & Reel
MC74HC273ADT	TSSOP-20*	75 Units / Rail
MC74HC273ADTG	TSSOP-20*	75 Units / Rail
MC74HC273ADTR2	TSSOP-20*	2500 Tape & Reel
MC74HC273ADTR2G	TSSOP-20*	2500 Tape & Reel
MC74HC273AF	SOEIAJ-20	40 Units / Rail
MC74HC273AFG	SOEIAJ-20 (Pb-Free)	40 Units / Rail
MC74HC273AFEL	SOEIAJ-20	2000 Tape & Reel
MC74HC273AFELG	SOEIAJ-20 (Pb-Free)	2000 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*This package is inherently Pb–Free.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
I <sub>in</sub>	DC Input Current, per Pin	± 20	mA
l <sub>out</sub>	DC Output Current, per Pin	± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 50	mA
P <sub>D</sub>	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{\text{in}}$  and Vout should be constrained to the range GND  $\leq$  (V<sub>in</sub> or V<sub>out</sub>)  $\leq$  V<sub>CC</sub>.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected. †Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)			6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)			V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Packa	ige Types	- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

# DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V <sub>CC</sub>	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out}  \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\begin{split} V_{in} = V_{IH} &  I_{out}  \leq 2.4 \text{ mA} \\  I_{out}  \leq 6.0 \text{ mA} \\  I_{out}  \leq 7.8 \text{ mA} \end{split}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out}  \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{split} V_{in} = V_{IL} & \qquad  I_{out}  \leq 2.4 \text{ mA} \\ &  I_{out}  \leq 6.0 \text{ mA} \\ &  I_{out}  \leq 7.8 \text{ mA} \end{split}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
l <sub>OZ</sub>	Maximum Three–State Leakage Current	Output in High–Impedance State $V_{in} = V_{IL}$ or $V_{IH}$ $V_{out} = V_{CC}$ or GND	6.0	± 0.5	± 5.0	± 10	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4.0	40	160	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6.0 \text{ ns}$ )

			Gu	Guaranteed Limit			
Symbol	Parameter	V <sub>CC</sub>	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit	
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	2.0 3.0 4.5 6.0	6.0 15 30 35	5.0 10 24 28	4.0 8.0 20 24	MHz	
t <sub>PLH</sub> t <sub>PHL</sub>	Maximum Propagation Delay, Clock to Q (Figures 1 and 4)	2.0 3.0 4.5 6.0	145 90 29 25	180 120 36 31	220 140 44 38	ns	
t <sub>PHL</sub>	Maximum Propagation Delay, Reset to Q (Figures 2 and 4)	2.0 3.0 4.5 6.0	145 90 29 25	180 120 36 31	220 140 44 38	ns	
t <sub>TLH</sub> t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns	
C <sub>in</sub>	Maximum Input Capacitance		10	10	10	pF	

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

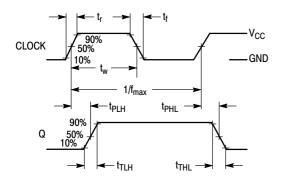
		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Enabled Output)*	48	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

# **TIMING REQUIREMENTS** ( $C_L = 50 \text{ pF}$ , Input $t_f = t_f = 6.0 \text{ ns}$ )

				Guaranteed Limit						
			v <sub>cc</sub>	– 55 to	25°C	≤ 8	5°C	≤ 12	25°C	
Symbol	Parameter	Figure	Volts	Min	Max	Min	Max	Min	Max	Unit
t <sub>su</sub>	Minimum Setup Time, Data to Clock	3	2.0 3.0 4.5 6.0	60 23 12 10		75 27 15 13		90 32 18 15		ns
t <sub>h</sub>	Minimum Hold Time, Clock to Data	3	2.0 3.0 4.5 6.0	3.0 3.0 3.0 3.0		3.0 3.0 3.0 3.0		3.0 3.0 3.0 3.0		ns
t <sub>rec</sub>	Minimum Recovery Time, Reset Inactive to Clock	2	2.0 3.0 4.5 6.0	5.0 5.0 5.0 5.0		5.0 5.0 5.0 5.0		5.0 5.0 5.0 5.0		ns
t <sub>w</sub>	Minimum Pulse Width, Clock	1	2.0 3.0 4.5 6.0	60 23 12 10		75 27 15 13		90 32 18 15		ns
t <sub>w</sub>	Minimum Pulse Width, Reset	2	2.0 3.0 4.5 6.0	60 23 12 10		75 27 15 13		90 32 18 15		ns
t <sub>r</sub> , t <sub>f</sub>	Maximum Input Rise and Fall Times	1	2.0 3.0 4.5 6.0		1000 800 500 400		1000 800 500 400		1000 800 500 400	ns

# **SWITCHING WAVEFORMS**



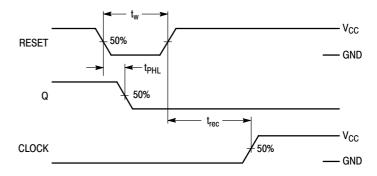


Figure 1.

Figure 2.

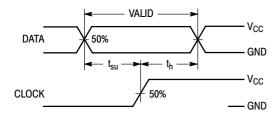
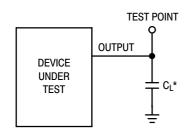


Figure 3.



\*Includes all probe and jig capacitance

Figure 4. Test Circuit

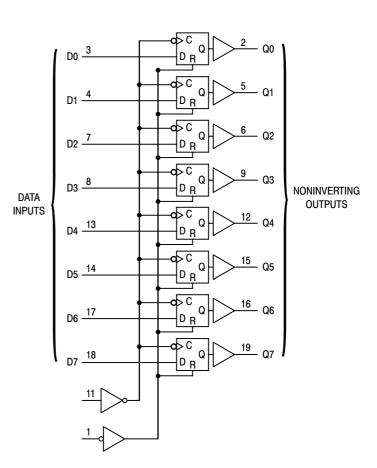
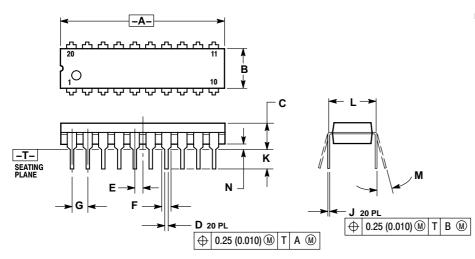


Figure 5. Expanded Logic Diagram

#### PACKAGE DIMENSIONS

# PDIP-20 **N SUFFIX** PLASTIC DIP PACKAGE CASE 738-03 **ISSUE E**



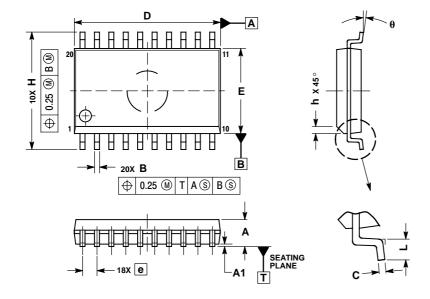
#### NOTES:

- (OLES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

- DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	INC	HES	MILLIN	ETERS
DIM	MIN	MAX	MIN	MAX
Α	1.010	1.070	25.66	27.17
В	0.240	0.260	6.10	6.60
С	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
E	0.050	BSC	1.27	BSC
F	0.050	0.070	1.27	1.77
G	0.100	BSC	2.54	BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300	BSC	7.62	BSC
М	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

# SOIC-20 **DW SUFFIX** CASE 751D-05 **ISSUE G**

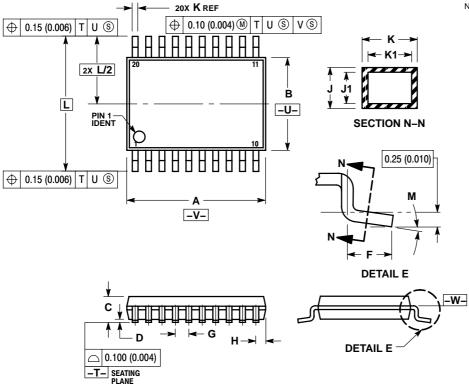


- NOTES:
  1. DIMENSIONS ARE IN MILLIMETERS.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
  5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
Е	7.40	7.60		
е	1.27 BSC			
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
Δ.	00	70		

#### **PACKAGE DIMENSIONS**

# TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE B**



#### NOTES:

- DTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SILLIAL NOT EXCEPT A 45 SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- SIDE.

  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER
- SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

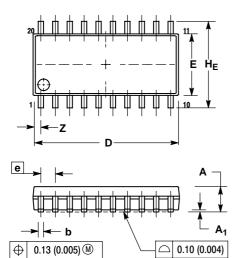
  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

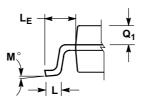
  6. TERMINAL NUMBERS ARE SHOWN.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

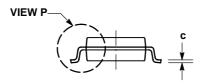
# **PACKAGE DIMENSIONS**

# SOEIAJ-20 **F SUFFIX** CASE 967-01 **ISSUE O**





**DETAIL P** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI

- NOTES:

  1 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2 CONTROLLING DIMENSION: MILLIMETER.

  3 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE RADIUS OR THE FOOT. MINIMUM SPACE
  BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 ( 0.018).

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
E	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
$Q_1$	0.70	0.90	0.028	0.035
Z		0.81		0.032

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